

## **TDA2822M**

## **DUAL LOW-VOLTAGE POWER AMPLIFIER**

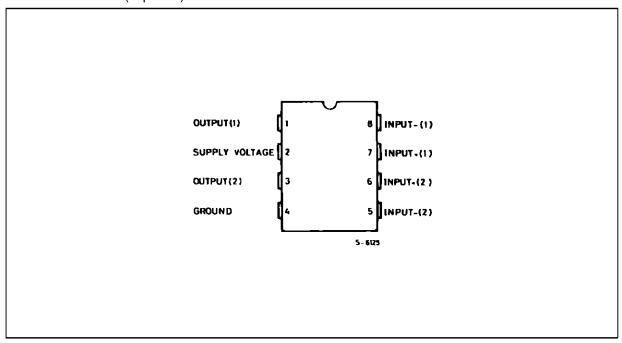
- SUPPLY VOLTAGE DOWN TO 1.8V
- LOW CROSSOVER DISTORSION
- LOW QUIESCENT CURRENT
- BRIDGE OR STEREO CONFIGURATION



#### **DESCRIPTION**

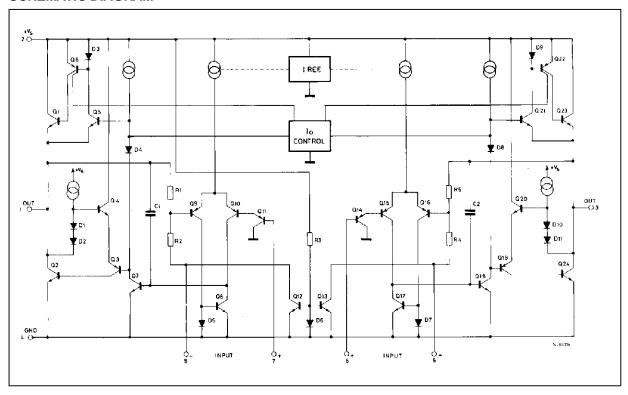
The TDA2822M is a monolithic integrated circuit in 8 lead Minidip package. It is intended for use as dual audio power amplifier in portable cassette players and radios.

#### **PIN CONNECTION** (Top view)



March 1995 1/11

#### **SCHEMATIC DIAGRAM**



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	15	V
Io	Peak Output Current	1	Α
P <sub>tot</sub>	Total Power Dissipation at T <sub>amb</sub> = 50 °C at T <sub>case</sub> = 50 °C	1 1.4	<b>&gt;</b>
T <sub>stg</sub> , T <sub>j</sub>	Storage and Junction Temperature	- 40, <b>+</b> 150	°C

#### **THERMAL DATA**

Symbol	Parameter	Value	Unit
R <sub>th j-amb</sub>	Thermal Resistance Junction-ambient Max	100	°C/W
R <sub>th j-case</sub>	Thermal Resistance Junction-pin (4) Max	. 70	°C/W

# ELECTRICAL CHARACTERISTICS (V<sub>S</sub> = 6V, T<sub>amb</sub> = 25°C, unless otherwise specified) Symbol Parameter Test Conditions Min Typ Max Unit

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit		
STEREO (test circuit of Figure 1)								
Vs	Supply Voltage		1.8		15	V		
Vo	Quiescent Output Voltage	V 2V		2.7		V		
1	Quicagent Proin Current	V <sub>s</sub> = 3V		1.2	9	V		
I <sub>d</sub>	Quiescent Drain Current Input Bias Current			100	9	mA nA		
Po	Output Power (each channel)			100		mW		
Fo	(f = 1kHz, d = 10%)	$\begin{array}{lll} R_L = 32\Omega & V_S = 9V \\ & V_S = 6V \\ & V_S = 4.5V \\ & V_S = 3V \\ & V_S = 2V \\ R_L = 16\Omega & V_S = 6V \\ R_L = 8\Omega & V_S = 9V \\ & V_S = 6V \\ R_L = 4\Omega & V_S = 6V \\ & V_S = 4.5V \\ & V_S = 3V \end{array}$	90 15 170 300 450	300 120 60 20 5 220 1000 380 650 320 110		IIIVV		
d	Distortion (f = 1kHz)	$\begin{array}{ll} R_L = 32\Omega & P_o = 40 \text{mW} \\ R_L = 16\Omega & P_o = 75 \text{mW} \\ R_L = 8\Omega & P_o = 150 \text{mW} \end{array}$		0.2 0.2 0.2		% % %		
Gv	Closed Loop Voltage Gain	f = 1kHz	36	39	41	dB		
$\Delta G_{v}$	Channel Balance				± 1	dB		
Ri	Input Resistance	f = 1kHz	100			kΩ		
e <sub>N</sub>	Total Input Noise	$R_s = 10k\Omega$ B = Curve A B = 22Hz to 22kHz		2 2.5		μV μV		
SVR	Supply Voltage Rejection	f = 100Hz, C1 = C2 = 100μF	24	30		dB		
Cs	Channel Separation	f = 1kHz		50		dB		
BRIDGE (t	test circuit of Figure 2)							
Vs	Supply Voltage		1.8		15	V		
I <sub>d</sub>	Quiescent Drain Current	R <sub>L</sub> = ∞		6	9	mA		
V <sub>os</sub>	Output Offset Voltage (between the outputs)	$R_L = 8\Omega$			± 50	mV		
I <sub>b</sub>	Input Bias Current			100		nA		
Po	Output Power (f = 1kHz, d = 10%)	$\begin{array}{lll} R_L = 32\Omega & V_S = 9V \\ & V_S = 6V \\ & V_S = 4.5V \\ & V_S = 3V \\ & V_S = 2V \\ R_L = 16\Omega & V_S = 9V \\ & V_S = 6V \\ & V_S = 3V \\ R_L = 8\Omega & V_S = 6V \\ & V_S = 3V \\ R_L = 4\Omega & V_S = 3V \\ & V_S = 3V \\ & V_S = 2V \\ \end{array}$	320 50 900 200	1000 400 200 65 8 2000 800 120 1350 700 220 1000 350 80		mW		
d	Distortion	$P_0 = 0.5W$ , $R_L = 8\Omega$ , $f = 1kHz$		0.2		%		
G <sub>v</sub>	Closed Loop Voltage Gain	f = 1kHz		39		dB		
Ri	Input Resistance	f = 1kHz	100			kΩ		
e <sub>N</sub>	Total Input Noise	$R_s = 10k\Omega$ B = Curve A B = 22Hz to 22kHz		2.5 3		μV μV		
SVR	Supply Voltage Rejection	f = 100Hz		40		dB		
В	Power Bandwidth (–3dB)	$R_L = 8\Omega, P_0 = 1W$		120		kHz		

Figure 1 : Test Circuit (Stereo)

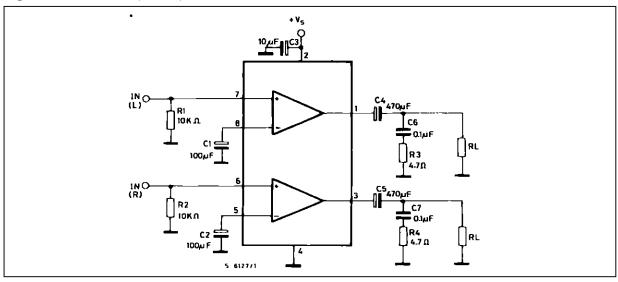
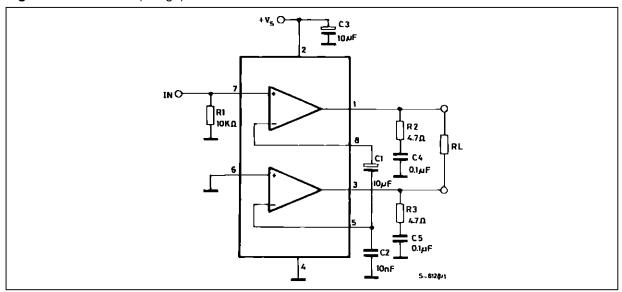
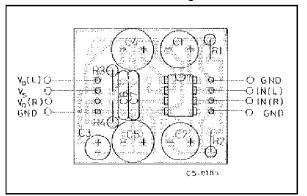


Figure 2: Test Circuit (Bridge)



**Figure 3 :** P.C. Board and Components Layout of the Circuit of Figure 1



**Figure 4 :** P.C. Board and Components Layout of the Circuit of Figure 2

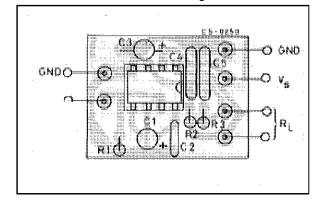
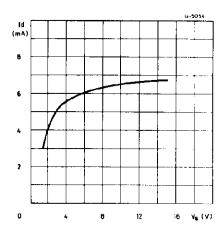
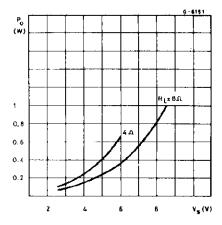


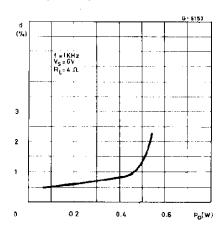
Figure 5 : Quiescent Current versus Supply Voltage



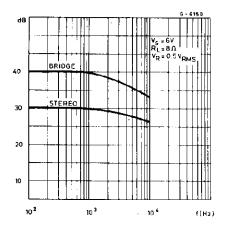
**Figure 7:** Output Power versus Supply Voltage (THD = 10%, f = 1kHz Stereo)



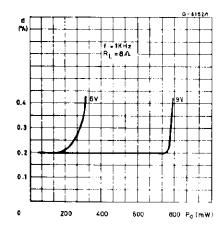
**Figure 9 :** Distorsion versus Output Power (Stereo)



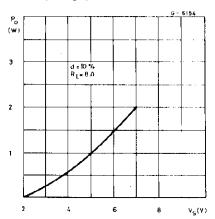
**Figure 6 :** Supply Voltage Rejection versus Frequency



**Figure 8 :** Distorsion versus Output Power (Stereo)



**Figure 10:** Output Power versus Supply Voltage (Bridge)



**Figure 11:** Distorsion versus Output Power (Bridge)

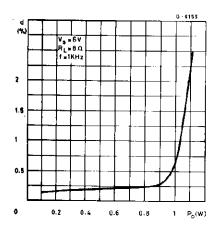


Figure 13: Total Power Dissipation versus Output Power (Bridge)

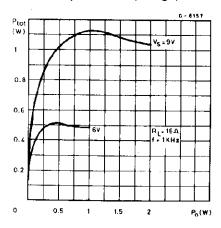


Figure 15: Total Power Dissipation versus Output Power (Bridge)

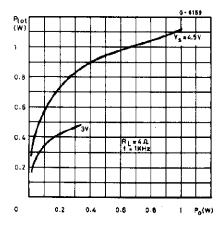
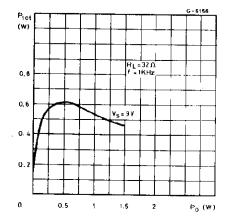
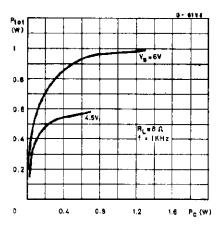


Figure 12: Total Power Dissipation versus Output Power (Bridge)



**Figure 14 :** Total Power Dissipation versus Output Power (Bridge)



S-6132/1

100µF

Figure 16: Typical Application in Portable Players

Figure 17: Application in Portable Radio Receivers

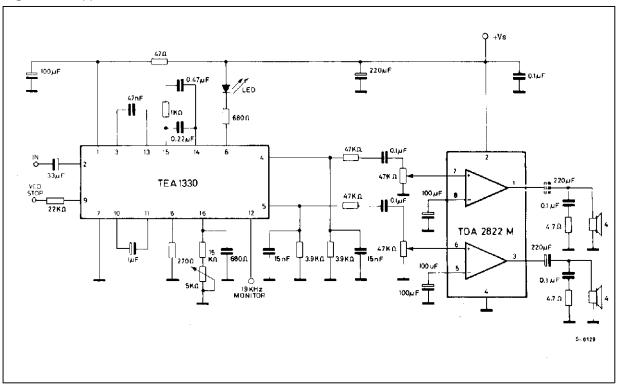


Figure 18: Portable Radio Cassette Players

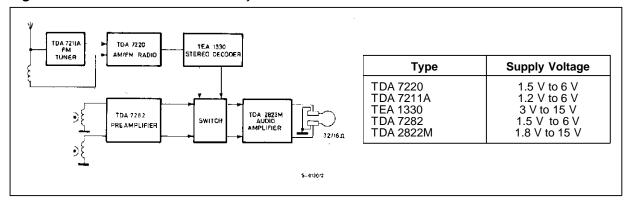


Figure 19: Portable Stereo Radios

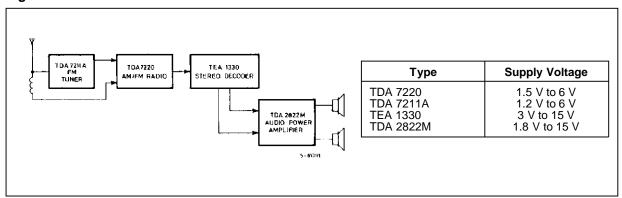
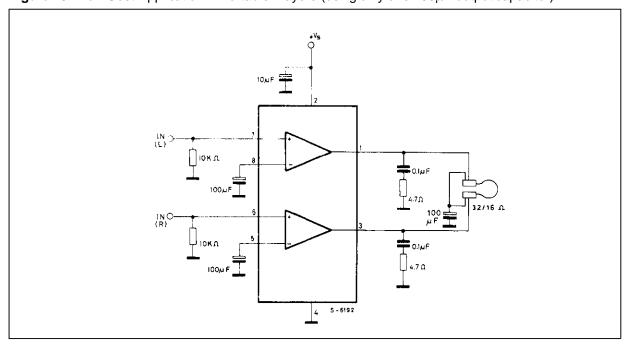


Figure 20: Low Cost Application in Portable Players (using only one 100μF output capacitor)



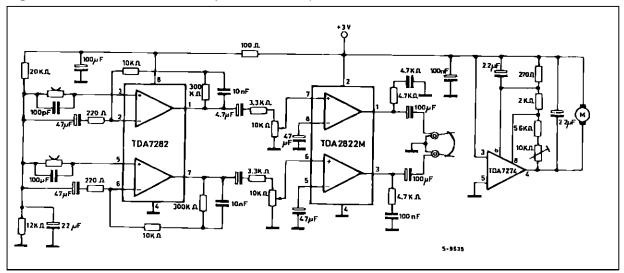
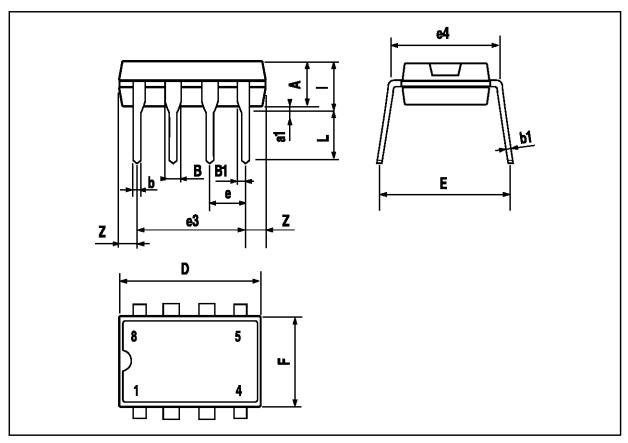


Figure 21: 3V Stereo Cassette Player with Motot Speed Control

### MINIDIP PACKAGE MECHANICAL DATA

DIM.		mm		inch		
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α		3.32			0.131	
a1	0.51			0.020		
В	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
Е	7.95		9.75	0.313		0.384
е		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060



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